

GJC650DA04是一款具有超高的开关频率、低栅极电荷、高功率密度的常关型(增强型) 器件

Parameter	Value	Unit
VDS,max	650	V
RDS(on),max	480	mΩ
QG,typ	0.9	nC
IDS,Pulse	10	A
QOSS @ 400V	8	nC
Qrr	0	nC

Type/Ordering Code	Package	Marking
XGC650DA04	DFN 5X6	GJC650DA04



器件产品目录

3、增强型功率器件-GJC650DA04

三、产品参数（静态）

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min	Typ	Max		
Gate threshold voltage	VGS(T _H)	0.8	1.3	1.8	V	ID = 5.2 mA; VDS = VGS; Tj = 25 °C
		-	1.6	-	V	ID =5.2 mA; VDS = VGS; Tj = 125 °C
Drain-source leakage current	IDSS	-	0.4	10	μA	VDS = 650 V; VGS = 0 V; Tj = 25 °C
		-	5	80	μA	VDS = 650 V; VGS = 0 V; Tj = 150 °C
Gate-source leakage current	IGSS	-	10	-	μA	VGS = 6 V; VDS = 0 V
Drain-source on-state resistance	RDS(o _n)	-	365	480	mΩ	VGS = 6 V; ID = 2A; Tj = 25 °C
		-	750	-	mΩ	VGS = 6 V; ID =2 A; Tj = 150 °C
Gate resistance	RG	-	3	-	Ω	F = 5 MHz; open drain

四、产品参数（动态）

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min	Typ	Max		
Input capacitance	Ciss	-	73	-	pF	VGS = 0 V; VDS = 400 V; f = 100 kHz
Output capacitance	Coss	-	20	-	pF	VGS = 0 V; VDS = 400 V; f = 100 kHz
Reverse transfer capacitance	Crss	-	0.2	-	pF	VGS = 0 V; VDS = 400 V; f = 100 kHz
Effective output capacitance, energy related 1	Co(er)	-	27	-	pF	VGS = 0 V; VDS = 0 to 400 V
Effective output capacitance, time related 2	Co(tr)	-	43	-	pF	VGS = 0 V; VDS = 0 to 400 V
Output Charge	QOSS	-	19	-	nC	VGS = 0 V; VDS = 0 to 400 V

